

TECHNICAL DATA  
DATA SHEET 5482, REV.

## Diode Array

- **Devices Are Serialized**
- **Eight sets of double diodes in a single package**
- **Die manufactured on qualified JANS line**
- **Built and screened to space level quality (SDA1009SS)**
- **Quality Conformance Inspection (QCI) in accordance with MIL-PRF-38534 is performed on each lot (SDA1009SS)**
- **Add suffix "S" for screening per MIL-PRF-38534, Class H (SDA1009S)**
- **Add suffix "SS" for Space Level Screening per MIL-PRF-38534, Class K (SDA1009SS)**
- **Each diode similar to JANS1N5615**

### MAX. RATINGS / ELECTRICAL CHARACTERISTICS FOR EACH DIODE

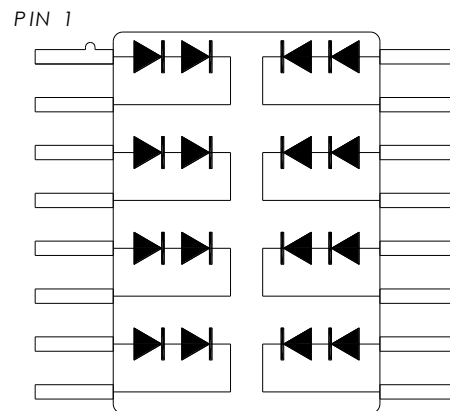
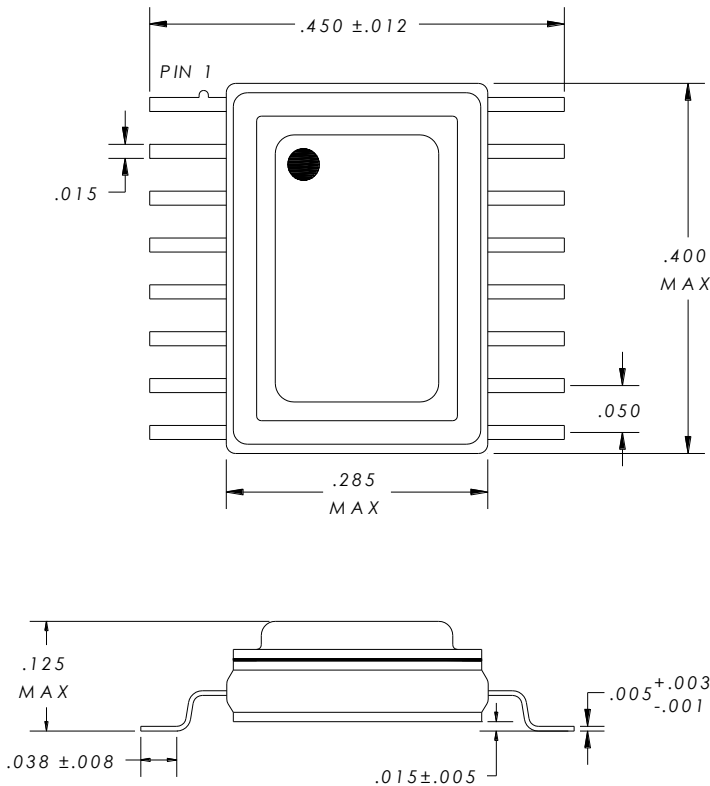
All rating at are  $T_A = 25^{\circ}\text{C}$  unless otherwise specified

RATING	SYMBOL	MAX	UNIT
Peak Inverse Voltage (DC)	PIV	400	V
Average DC Output Current Per Diode $T_A = 55^{\circ}\text{C}$ $T_A = 100^{\circ}\text{C}$	$I_O$	1 0.75	A
Peak Single Cycle Surge Current <sup>(1)</sup> ( $T_P=8.3\text{ms}$ single half-Sine wave)	$I_{FSM}$	10	A
Steady State Power Dissipation per Package <sup>(2)</sup>	$P_T$	1000	mW
Max. Operating Junction Temperature	$T_J$	-55 to +150	$^{\circ}\text{C}$
Max. Operating Ambient Temperature	$T_{OP}$	-30 to 100	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-65 to +175	$^{\circ}\text{C}$
Maximum forward voltage @ 3.0A $T_p = 300\mu\text{s}$ ; 2% duty cycle	$V_f$	3.2	V
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^{\circ}\text{C}$ $T_A = 100^{\circ}\text{C}$	0.5 25	$\mu\text{A}$
Max. Reverse Recovery Time $I_F = 0.5\text{ A}$ , $I_R = 1.0\text{A}$ , $I_{RR} = 0.25\text{A}$	$t_{rr}$	150	ns
Max. Capacitance $f = 1\text{MHz}$ , $V_R = 12\text{V}$	$C_T$	30	pF
Thermal Resistance Junction to Case	$\theta_{JC}$	21	$^{\circ}\text{C/W}$

Note: (1) Each diode  
(2) Derate at  $8\text{mW}/^{\circ}\text{C}$  above  $25^{\circ}\text{C}$

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**Mechanical Outline**



**Electrical Schematic**

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